

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type (PCT process)

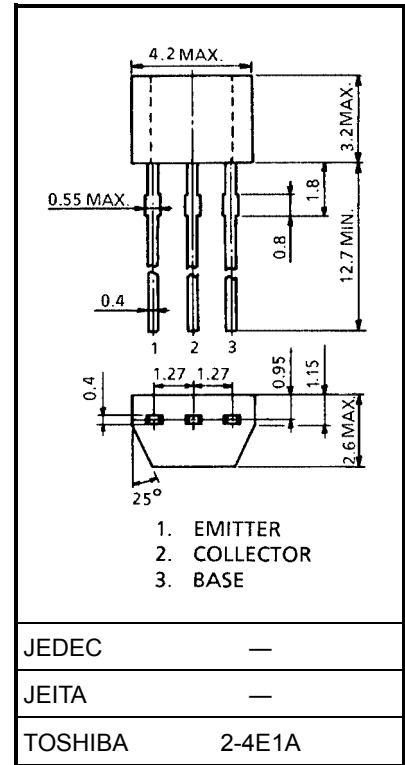
2SC2669

High Frequency Amplifier Applications

- High power gain: $G_{pe} = 30\text{dB}$ (typ.) ($f = 10.7\text{ MHz}$)
- Recommended for FM IF, OSC stage and AM CONV, IF stage.

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	35	V
Collector-emitter voltage	V_{CEO}	30	V
Emitter-base voltage	V_{EBO}	4	V
Collector current	I_C	50	mA
Base current	I_B	10	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~125	$^\circ\text{C}$



Weight: 0.13 g (typ.)

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 35\text{ V}, I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4\text{ V}, I_C = 0$	—	—	1.0	μA
DC current gain	h_{FE} (Note)	$V_{CE} = 12\text{ V}, I_C = 2\text{ mA}$	40	—	240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10\text{ mA}, I_B = 1\text{ mA}$	—	—	0.4	V
Base-emitter voltage	V_{BE}	$I_C = 10\text{ mA}, I_B = 1\text{ mA}$	—	—	1.0	V
Transition frequency	f_T	$V_{CE} = 10\text{ V}, I_C = 1\text{ mA}$	100	—	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	2.0	3.2	pF
Collector-base time constant	$C_c \cdot r_{bb'}$	$V_{CE} = 10\text{ V}, I_E = -1\text{ mA}, f = 30\text{ MHz}$	—	—	50	ps
Power gain	G_{pe}	$V_{CC} = 6\text{ V}, I_E = -1\text{ mA}, f = 10.7\text{ MHz}$ (Figure 1)	27	30	33	dB

Note: h_{FE} classification R: 40~80, O: 70~140, Y: 120~240

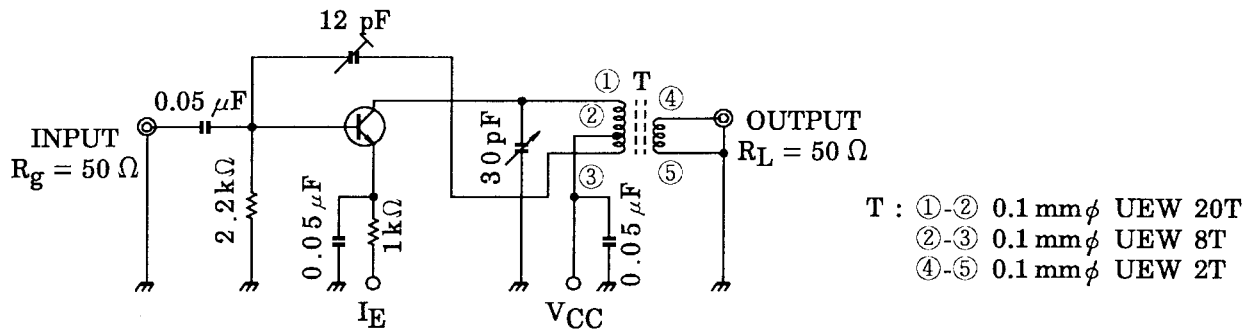


Figure 1 G_{pe} Test Circuit

Y Parameters (typ.)

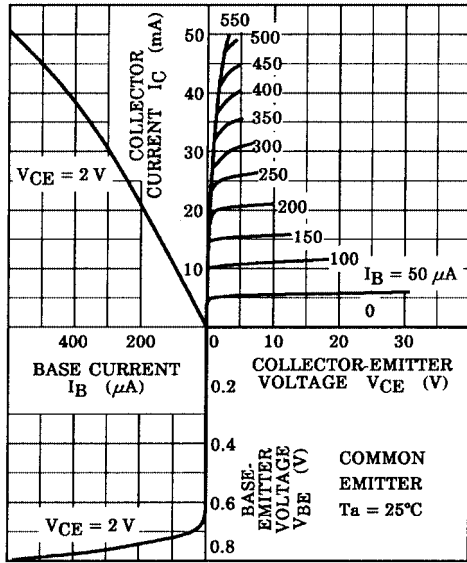
(1) (common emitter f = 455 kHz, Ta = 25°C)

Characteristics	Symbol	2SC2669-R	2SC2669-O	2SC2669-Y	Unit
Collector-emitter voltage	V _{CE}	6	6	6	V
Emitter current	I _E	-1	-1	-1	mA
Input conductance	g _{ie}	0.58	0.41	0.26	mS
Input capacitance	C _{ie}	53	46	38	pF
Output conductance	g _{oe}	1.9	2.7	4.8	μS
Output capacitance	C _{oe}	2.6	2.8	3.6	pF
Forward transfer admittance	y _{fe}	38	38	38	mS
Phase angle of forward transfer admittance	θ _{fe}	-0.79	-0.83	-0.92	°
Reverse transfer admittance	y _{re}	5.7	5.7	6.2	μS
Phase angle of reverse transfer admittance	θ _{re}	-90	-90	-90	°

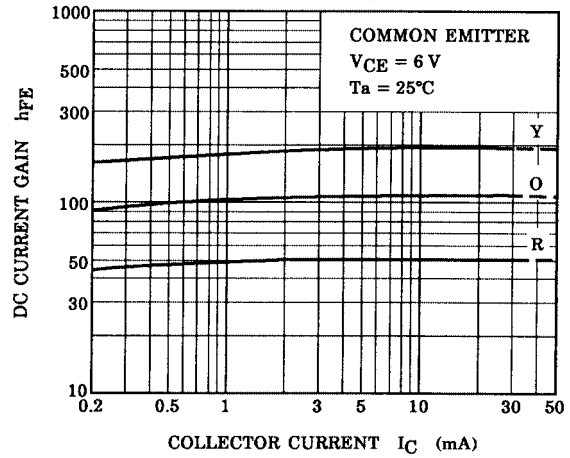
(2) (common emitter f = 10.7 MHz, Ta = 25°C)

Characteristics	Symbol	2SC2669-R	2SC2669-O	2SC2669-Y	Unit
Collector-emitter voltage	V _{CE}	6	6	6	V
Emitter current	I _E	-1	-1	-1	mA
Input conductance	g _{ie}	1.04	0.85	0.65	mS
Input capacitance	C _{ie}	49	43	36	pF
Output conductance	g _{oe}	10	15	28	μS
Output capacitance	C _{oe}	2.7	2.9	3.6	pF
Forward transfer admittance	y _{fe}	37	37	37	mS
Phase angle of forward transfer admittance	θ _{fe}	-9.6	-10.4	-11.5	°
Reverse transfer admittance	y _{re}	120	120	140	μS
Phase angle of reverse transfer admittance	θ _{re}	-90	-90	-90	°

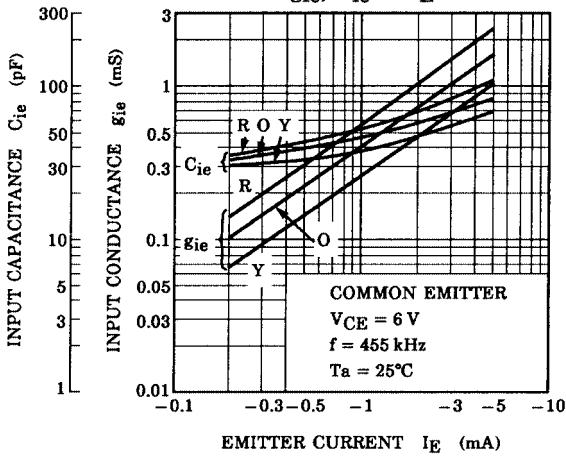
STATIC CHARACTERISTICS



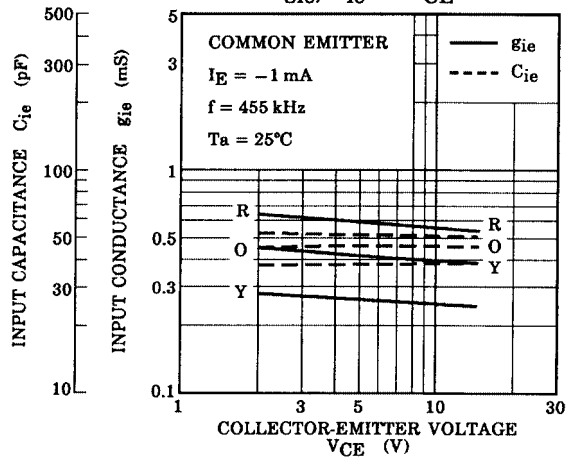
hFE - IC

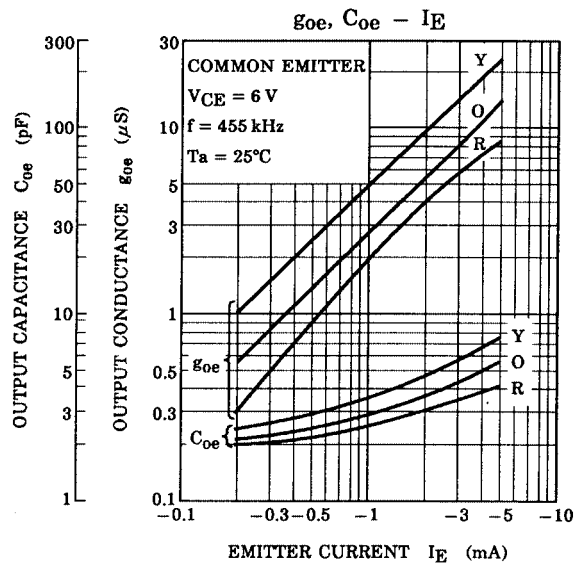
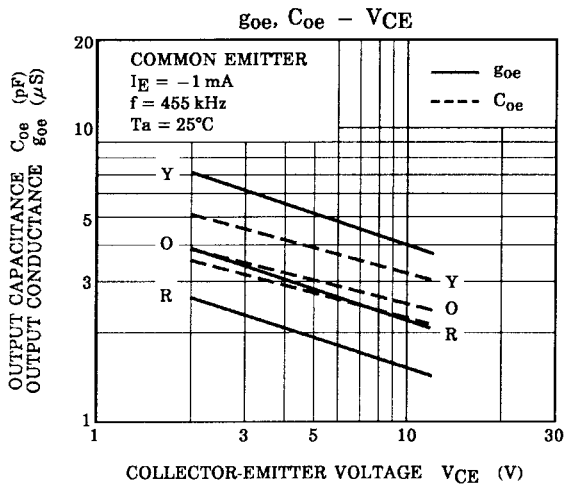
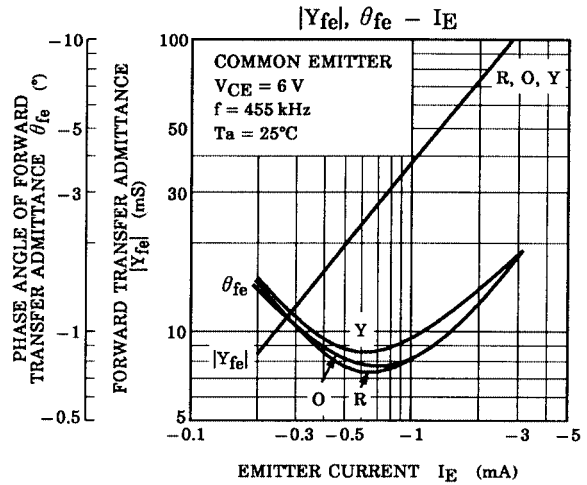
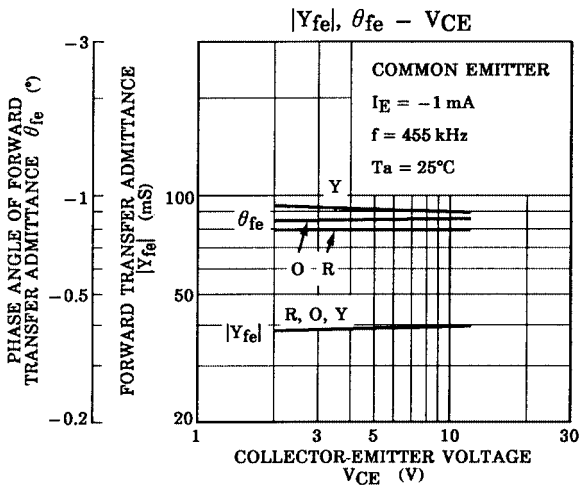
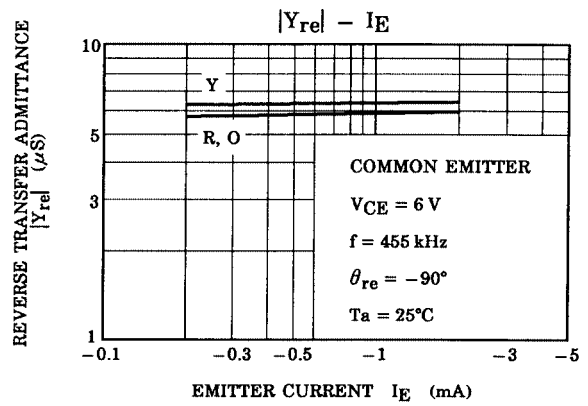
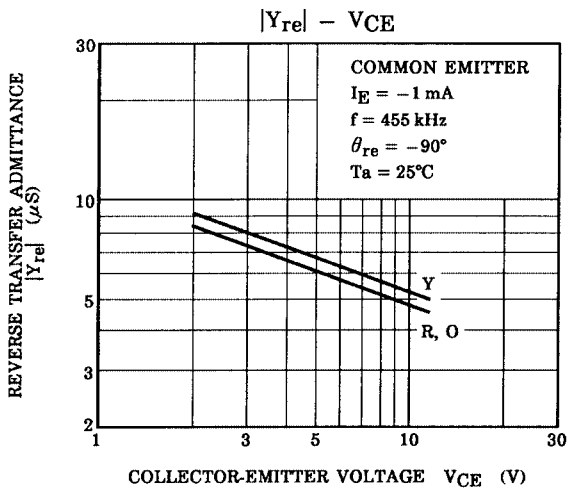


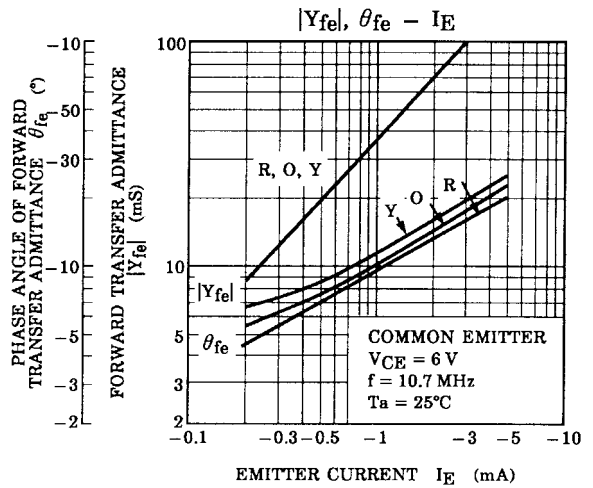
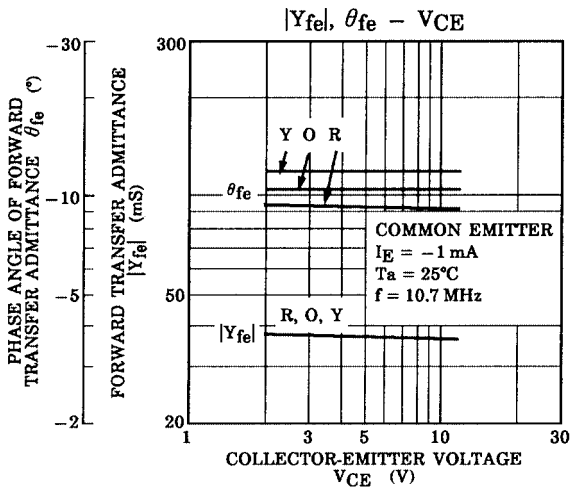
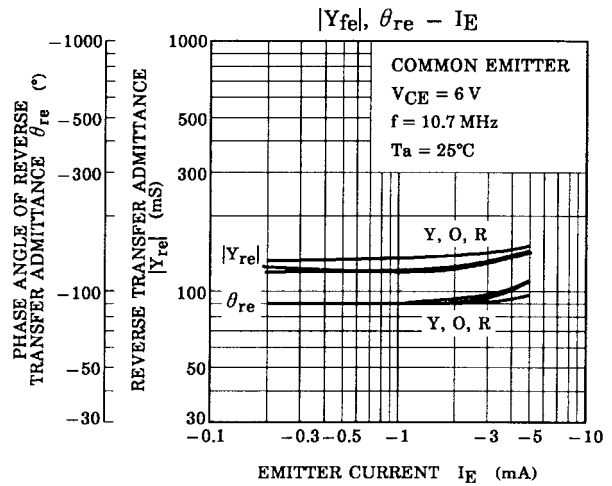
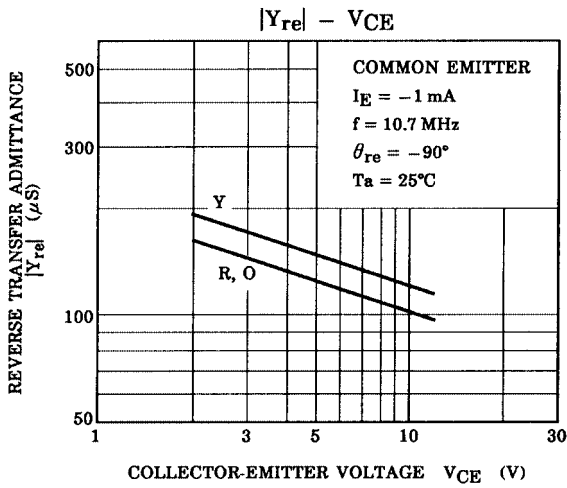
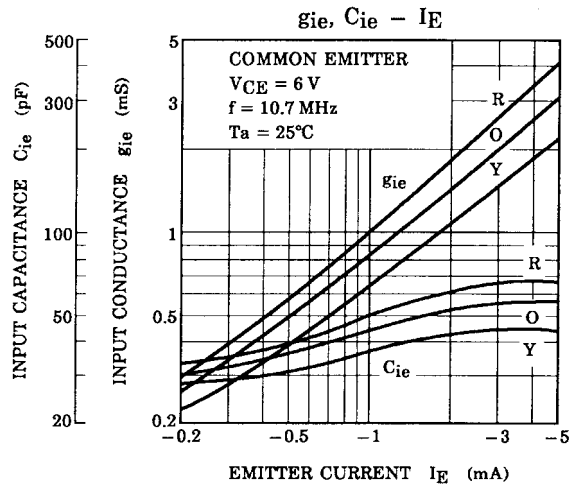
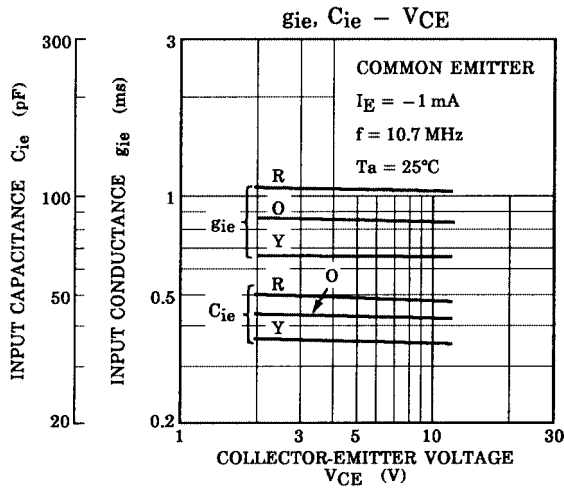
$g_{ie}, C_{ie} - I_E$

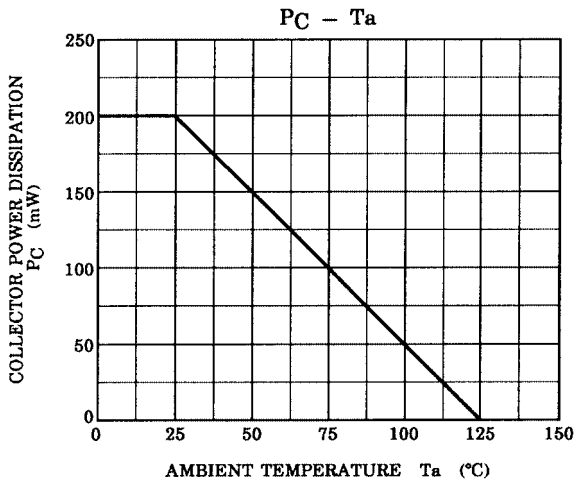
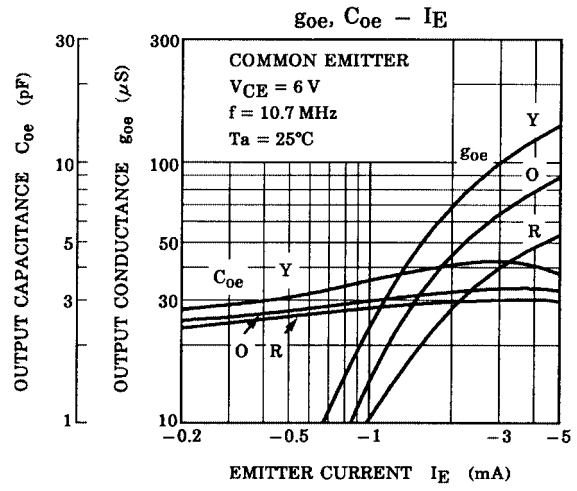
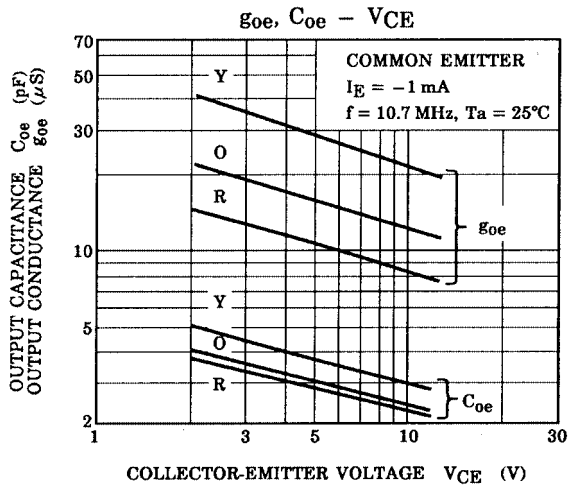


$g_{ie}, C_{ie} - V_{CE}$









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